



# **Linear Ion Beam Sources**



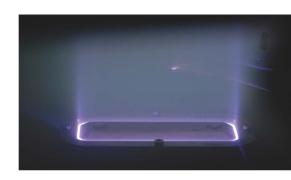
Linear ion sources generate wide ion beams with high uniformity along its length. These anode layer type ion beam sources are very reliable and robust devices that can be operated with a wide range of gases and mixtures. They don't need an extra neutralizer for charge compensation and thus are able to continuously operate using chemically active gases (oxygen, air, halogens, etc.). The source electrodes have almost unlimited lifetime when working with oxygen. For many applications air can be used instead of oxygen.

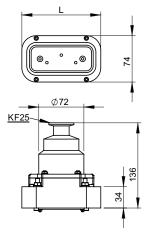
#### **Applications:**

- · Ion cleaning, ion etching
- Ion beam sputtering (IBS)
- Ion beam assisted deposition (IBAD)
- PECVD & DLC deposition
- Surface modification

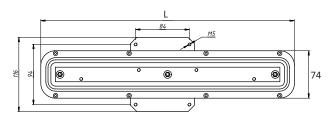
#### **Features**

- Compact linear design
- · Internal and flange mount versions
- · Long electrode life time
- · Self-neutralized ion beam
- High ion density
- Compatible with a wide range of gases
- Wide pressure range up to 1E-1 mBar





Dimensions for L125 / L145



Dimensions for L400, L600, L800







L145 flange mount on ISO160K

## Mounting configurations

All linear ion sources are available for internal and external mount configurations. Internally mount sources include a single KF25 utility port. A tilting head option with variable penetration depth e.g. for ion assist in confocal sputtering applications can be ordered for the smaller L125 and L145 sources.

## Power supply package

Along with the inverted magnetron ion sources we provide dedicated voltage or current controlled power supplies. When utilizing its integrated gas control feature both ion beam current and anode voltage can be kept constant.



Power supply IM300

D52	L125	L145	L400	L600	L800
500 5000					
	Approx. 1/2 of supply voltage				
150	300	350	1000	1500	2000
8	10				
Tubular	Hollow rectangular				
D22	100x42	120x42	375x42	575x42	775x42
D52	126	146	396	600	800
ISO63K	ISO160K	ISO160K	480 x 186	684 x 186	884 x 186
2°					
1E-5 to 1E-1					
Ar, H <sub>2</sub> , He, Xe, O <sub>2</sub> , N <sub>2</sub> , C <sub>x</sub> H <sub>y</sub> , CO <sub>2</sub> , C <sub>x</sub> F <sub>y</sub>					
	150 8 Tubular D22 D52	Ap 150 300 8 Tubular D22 100x42 D52 126 ISO63K ISO160K	500 .  Approx. 1/2 of  150 300 350  8  Tubular Ho  D22 100x42 120x42  D52 126 146  ISO63K ISO160K ISO160K	S00 5000	S00 5000   S000   S000

<sup>\*</sup> Parameters measured under the following conditions: Argon, voltage 3kV, pressure 1E-3 mBar

## Circular ion source D52

Apart from the linear sources the circular ion source D52 provides a tubular beam profile with 22 mm in diameter and small divergence. Thus it is ideal for ion beam sputtering or etching applications onto small targets or substrates while offering high ion energies with up to 150 mA ion beam current.



Circular ion source D52



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